## Electronic Supplementary Material (ESI) for Journal of Materials Chemistry B

## Electrodeposited NaYF<sub>4</sub>: Yb<sup>3+</sup>, Er<sup>3+</sup> up-conversion films for flexible neural device construction and near-infrared optogenetics

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**Figure S1.** Schematics of flexible device fabrication process. (i) Silicon substrate. The side view corresponds to the position of the white dotted line. (ii) Deposition of aluminum sacrifice layer. (iii) Spin-coating of bottom PI layer. (iv) Deposition and patterning of gold layer for filament and microelectrodes. (v) Spin-coating of middle PI layer. (vi) Patterning and deposition of gold layer for electrodeposition of NaYF<sub>4</sub>: Yb<sup>3+</sup>, Er<sup>3+</sup> film. (vii) Electrodeposition of NaYF<sub>4</sub>: Yb<sup>3+</sup>, Er<sup>3+</sup> film. (vii) Spin-coating of PI layer. (ix) RIE patterning of PI to form the flexible device and expose the recording sites. (x) Etching of aluminum to release the flexible device.



**Figure S2.** XPS spectrum of NaYF<sub>4</sub>: Yb<sup>3+</sup>, Er<sup>3+</sup> film. (a) XPS survey spectrum of NaYF<sub>4</sub>: Yb<sup>3+</sup>, Er<sup>3+</sup> film. (b) Local spectra for Na1s analyses of NaYF<sub>4</sub>: Yb<sup>3+</sup>, Er<sup>3+</sup> film. (c) Local spectra for F1s analyses of NaYF<sub>4</sub>: Yb<sup>3+</sup>, Er<sup>3+</sup> film. (d) Local spectra for Y3d analyses of NaYF<sub>4</sub>: Yb<sup>3+</sup>, Er<sup>3+</sup> film. (e) Local spectra for Yb4d analyses of NaYF<sub>4</sub>: Yb<sup>3+</sup>, Er<sup>3+</sup> film.



Figure S3. Schematic diagram of crystal structure of  $\alpha$ -NaYF<sub>4</sub> (Left) and  $\beta$ -NaYF<sub>4</sub> (Right).



**Figure S4.** Fluorescence spectra in visible spectrum of UC films prepared at different  $F^{-}/R^{3+}$  ratios on the ITO substrate.



**Figure S5.** Photographs of a flip chip-bonded flexible neural device connected to a custom-designed PCB (Left, scale bar, 10 mm), and a self-assembled and packaged flexible neural device (Right, scale bar, 10 mm).



Figure S6. EIS of a recording site before (black) and after (red) nano-sized platinum electrodeposition.